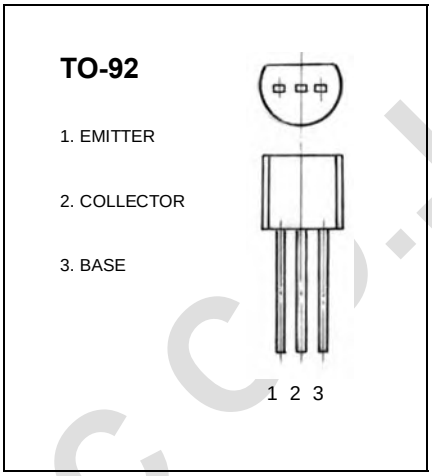
A1015 TRANSISTOR (PNP)



FEATURES

Power dissipation

$P_{CM:}$ 0.4 W (Tamb=25℃)

Collector current

$I_{CM:}$ -0.15 A

Collector-base voltage

$V_{(BR)CBO}$: -50 V

Operating and storage junction temperature range

T_J, T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V(BR)_{CBO}$	Ic= -100μA, I_E=0	-50			V
Collector-emitter breakdown voltage	$V(BR)_{CEO}$	Ic= -0. 1mA, I_B=0	-50			V
Emitter-base breakdown voltage	$V(BR)_{EBO}$	I_E= -100μA, I_C=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}= -50V, I_E=0			-0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}= -5V, I_C=0			-0.1	μA
DC current gain	$h_{FE(1)}$	V_{CE}= -6V, I_C= -2mA	70		400	
Collector-emitter saturation voltage	V_{CE}(sat)	I_C=-100mA, I_B= -10 mA			-0.3	V
Base-emitter saturation voltage	V_{BE}(sat)	I_C=-100 mA, I_B= -10mA			-1.1	V
Transition frequency	f_T	V_{CE}= -10 V, I_C= -1 mA f =30MHz	80			MHz

CLASSIFICATION OF $h_{FE(1)}$

Rank	O	Y	GR
Range	70-140	120-240	200-400